Silicon Power Transistors

The MJ15023 and MJ15025 are PowerBase power transistors designed for high power audio, disk head positioners and other linear applications.

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- High Safe Operating Area (100% Tested) 2 A @ 80 V
- High DC Current Gain —
 hFE = 15 (Min) @ IC = 8 Adc

MJ15023 MJ15025*

*Motorola Preferred Device

16 AMPERE SILICON POWER TRANSISTORS 200 AND 250 VOLTS 250 WATTS



CASE 1-07 TO-204AA (TO-3)

MAXIMUM RATINGS

Rating	Symbol	MJ15023	MJ15025	Unit
Collector–Emitter Voltage	VCEO	200	250	Vdc
Collector-Base Voltage	V _{CBO}	350	400	Vdc
Emitter-Base Voltage	VEBO	5		Vdc
Collector–Emitter Voltage	VCEX	400		Vdc
Collector Current — Continuous Peak (1)	Ic	16 30		Adc
Base Current — Continuous	I _B	5		Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	250 1.43		Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R ₀ JC	0.70	°C/W

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.



MJ15023 MJ15025

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					•
Collector–Emitter Sustaining Voltage (1) (I _C = 100 mAdc, I _B = 0)	MJ15023 MJ15025	VCEO(sus)	200 250	_ _	
Collector Cutoff Current (V _{CE} = 200 Vdc, V _{BE} (off) = 1.5 Vdc) (V _{CE} = 250 Vdc, V _{BE} (off) = 1.5 Vdc)	MJ15023 MJ15025	ICEX	_ _	250 250	μAdc
Collector Cutoff Current (V _{CE} = 150 Vdc, I _B = 0) (V _{CE} = 200 Vdc, I _B = 0)	MJ15023 MJ15025	ICEO		500 500	μAdc
Emitter Cutoff Current (V _{CE} = 5 Vdc, I _B = 0)	Both	I _{EBO}	_	500	μAdc
SECOND BREAKDOWN					
Second Breakdown Collector Current with Base Forward Biased ($V_{CE} = 50 \text{ Vdc}$, $t = 0.5 \text{ s (non-repetitive)}$) ($V_{CE} = 80 \text{ Vdc}$, $t = 0.5 \text{ s (non-repetitive)}$)		I _{S/b}	5 2	_ _	Adc
ON CHARACTERISTICS					
DC Current Gain (I _C = 8 Adc, V _{CE} = 4 Vdc) (I _C = 16 Adc, V _{CE} = 4 Vdc)		hFE	15 5	60 —	_
Collector–Emitter Saturation Voltage (I _C = 8 Adc, I _B = 0.8 Adc) (I _C = 16 Adc, I _B = 3.2 Adc)		VCE(sat)	_	1.4 4.0	Vdc
Base–Emitter On Voltage (I _C = 8 Adc, V _{CE} = 4 Vdc)		VBE(on)	_	2.2	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I _C = 1 Adc, V _{CE} = 10 Vdc, f _{test} = 1 MHz)		fT	4	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)		C _{ob}	_	600	pF

⁽¹⁾ Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%.

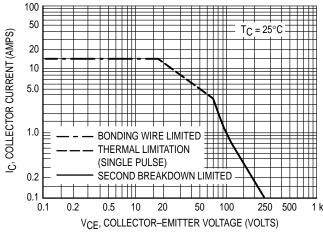


Figure 1. Active-Region Safe Operating Area

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC – VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

TYPICAL CHARACTERISTICS

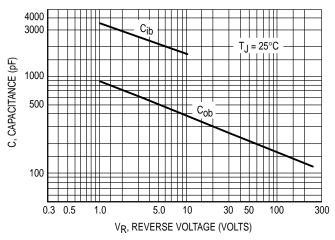


Figure 2. Capacitances

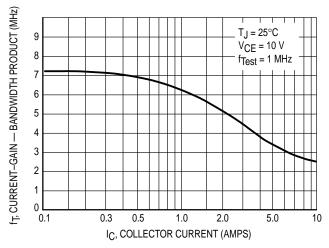


Figure 3. Current-Gain — Bandwidth Product

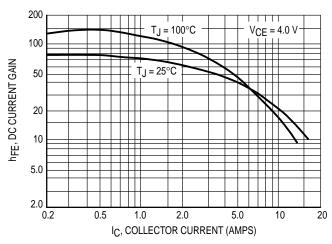


Figure 4. DC Current Gain

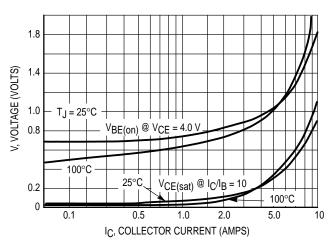
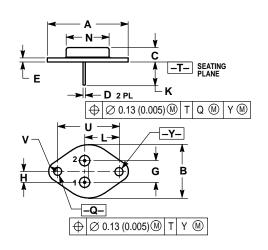


Figure 5. "On" Voltages

PACKAGE DIMENSIONS



NOTES:

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- 2. CONTROLLING DIMENSION: INCH.
- ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37 REF		
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
Е	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187 BSC		30.15 BSC		
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

CASE 1-07 TO-204AA (TO-3) ISSUE Z

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